

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device comprising:
a support base interposed between a pair of first adhesives;
a thin film integrated circuit, an antenna, and a separating layer over the support base pair of first adhesives; ~~[[and]]~~
a wiring electrically connecting the thin film integrated circuit and the ~~antenna~~,
antenna;
a second adhesive over the wiring; and
a cover material over the second adhesive,
wherein the wiring passes through the separating layer.
2. (Currently Amended) A semiconductor device comprising:
a support base interposed between a pair of first adhesives;
a thin film integrated circuit, a separating layer, and an antenna sequentially laminated over the support base pair of first adhesives; ~~[[and]]~~
a wiring electrically connecting the thin film integrated circuit and the ~~antenna~~,
antenna;
a second adhesive over the wiring; and
a cover material over the second adhesive,
wherein the wiring passes through the separating layer.
3. (Currently Amended) A semiconductor device comprising:
a support base interposed between a pair of first adhesives;

a thin film integrated circuit, an antenna, and a separating layer over the support base pair of first adhesives, wherein the thin film integrated circuit comprises a plurality of semiconductor elements; ~~[[and]]~~

a wiring electrically connecting the plurality of semiconductor elements, elements;

a second adhesive over the wiring; and

a cover material over the second adhesive,

wherein the wiring passes through the separating layer.

4. (Original) A semiconductor device according to any one of claims 1 to 3, wherein the antenna is formed by one of a printing method and a droplet discharging method.

5. (Currently Amended) A semiconductor device according to ~~any one of claims 1 to claim~~ claim 3, wherein the plurality of semiconductor elements comprise thin film transistors, wherein each of the thin film transistors comprises a semiconductor film and a gate electrode with a gate insulating film interposed therebetween.

6. (Original) A semiconductor device according to claim 5, wherein the antenna and the gate electrode are formed by patterning a same conductive film.

7. (Currently Amended) A semiconductor device according to any one of claims 1 to 3, wherein the thin film integrated circuit and the antenna are formed over a substrate and then peeled off by removing the substrate, and stuck to the support base using ~~an adhesive~~ one of the pair of first adhesives.

8. (Currently Amended) A semiconductor device comprising:
a support base interposed between a pair of first adhesives; ~~[[and]]~~

a thin film integrated circuit, an antenna, and a separating layer over the support base, pair of first adhesives;

a second adhesive over the antenna; and

a cover material over the second adhesive.

wherein the antenna comprises a plurality of wirings connected in series, and wherein at least one of the plurality of wirings passes through the separating layer.

9. (Currently Amended) A semiconductor device according to claim 8, wherein the thin film integrated circuit and the antenna are formed over a substrate and then peeled off the substrate by removing the substrate, and stuck to the support base using an adhesive one of the pair of first adhesives.

10. (Currently Amended) A semiconductor device comprising:

a support base interposed between a pair of first adhesives; [[and]]

a thin film integrated circuit, an antenna, and a separating layer sequentially laminated over the support base, pair of first adhesives;

a second adhesive over the antenna; and

a cover material over the second adhesive.

wherein the antenna comprises a plurality of wirings connected in series, and wherein at least one of the plurality of wirings passes through the separating layer.

11. (Currently Amended) A semiconductor device according to claim 10, wherein the thin film integrated circuit and the antenna are formed over a substrate and then peeled off the substrate by removing the substrate, and stuck to the support base using an adhesive one of the pair of first adhesives.

12. (Original) A semiconductor device according to any one of claims 1 to 3, 8 and 10, wherein the separating layer comprises a metal oxide film containing at least one selected from the group consisting of TiN, WN, Mo and W.

13. (Original) A semiconductor device according to claim 12, wherein the metal oxide film is in a crystalline state.

14. (Original) A semiconductor device according to any one of claims 1 to 3, 8 and 10, wherein the support base comprises at least one of a plastic and a paper.

15. (Original) A semiconductor device according to any one of claims 1 to 3, 8 and 10, wherein the semiconductor device is stuck to an object selected from the group consisting of a container, an envelope, a check and a passport.